

• General Description

The ZM074N04N combines trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

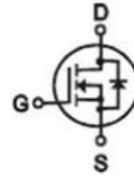
• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

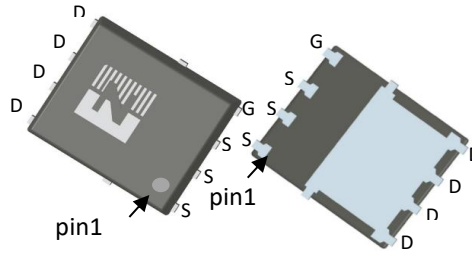
• Product Summary



$$V_{DS} = 40V$$

$$R_{DS(ON)} = 8m\Omega$$

$$I_D = 60A$$



DFN5 x 6



• Ordering Information:

Part NO.	ZM074N04N
Marking	ZM074N04
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	60	A
	$I_{D@TC=75^\circ C}$	45.6	A
	$I_{D@TC=100^\circ C}$	37.8	A
Pulsed Drain Current ^①	I_{DM}	150	A
Total Power Dissipation ^②	P_D	85	W
Total Power Dissipation($T_A = 25^\circ C$)	$P_{D@T_A=25^\circ C}$	3.4	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	140	mJ

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R_{thJC}	-	-	1.5	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	37	°C/W
Soldering temperature, wave soldering for 10s	T_{sld}	-	-	265	°C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=24A$		8	10.4	m Ω
		$V_{GS}=4.5V, I_D=12A$		13	16	m Ω
Forward Trans conductance	g_{FS}	$V_{DS}=25V, I_D=10A$		30		S
Source-drain voltage	V_{SD}	$I_S=24A$			1.28	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz V _{DS} =25V	-	1650	-	pF
Output capacitance	C_{oss}		-	260	-	
Reverse transfer capacitance	C_{rss}		-	140	-	

●Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD}=25V$	-	27	-	nC
Gate - Source charge	Q_{gs}	$I_D=15A$	-	8.6	-	
Gate - Drain charge	Q_{gd}	$V_{GS}=10V$	-	13.8	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Power Dissipation

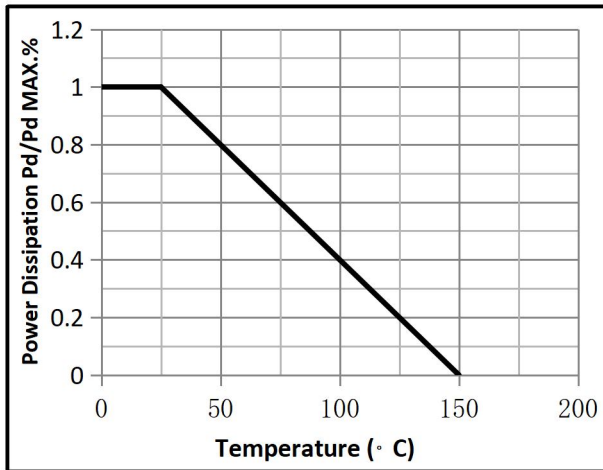


Fig.2 Typical output Characteristics

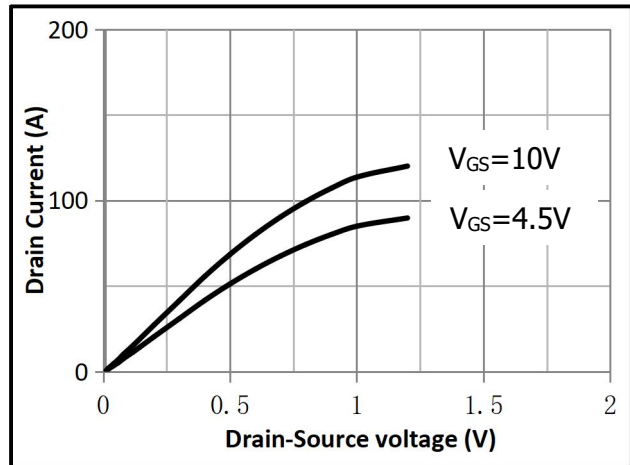


Fig.3 Threshold Voltage V.S Junction Temperature

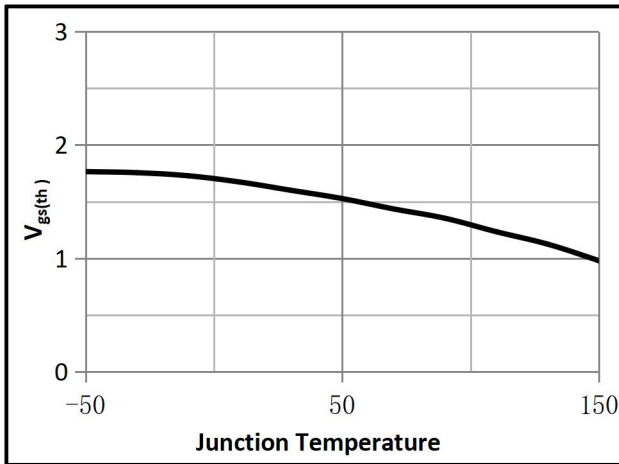


Fig.4 Resistance V.S Drain Current

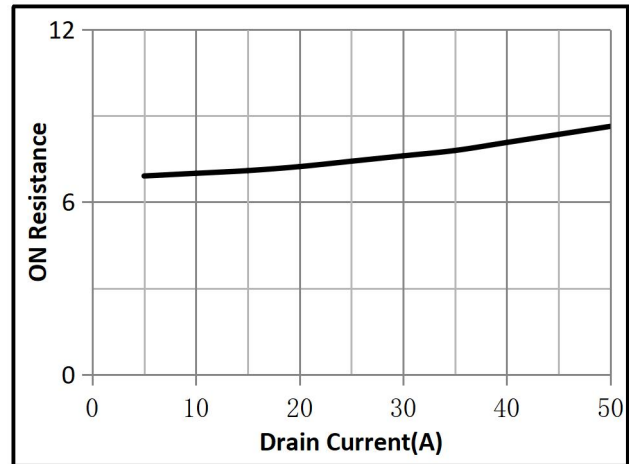


Fig.5 On-Resistance VS Gate Source Voltage

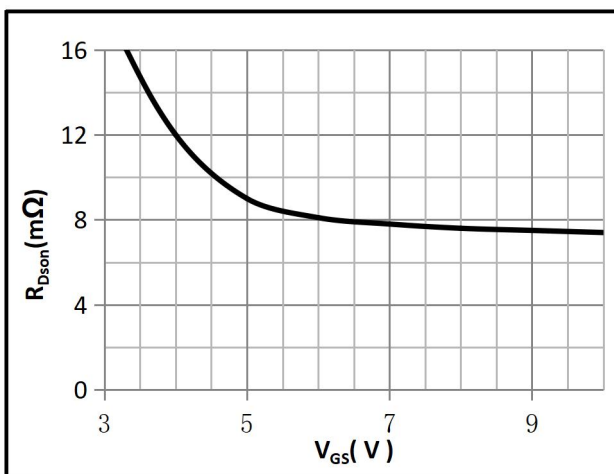


Fig.6 On-Resistance V.S Junction Temperature

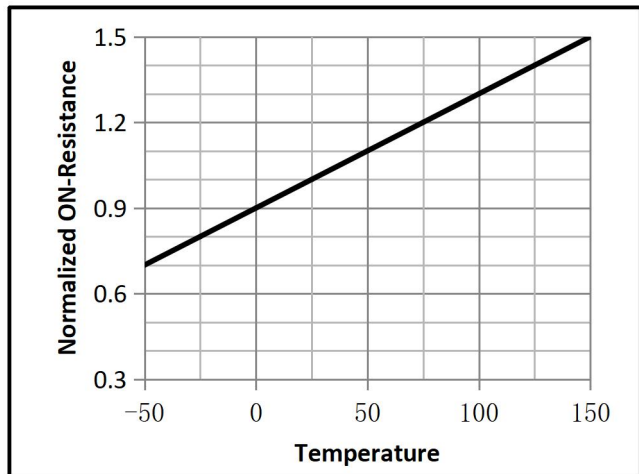


Fig.7 Switching Time Measurement Circuit

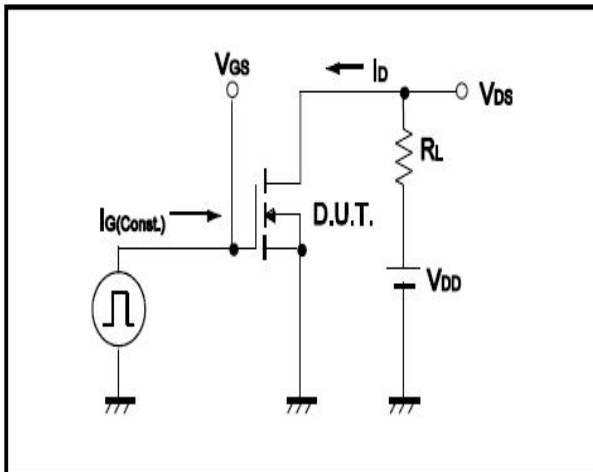


Fig.8 Gate Charge Waveform

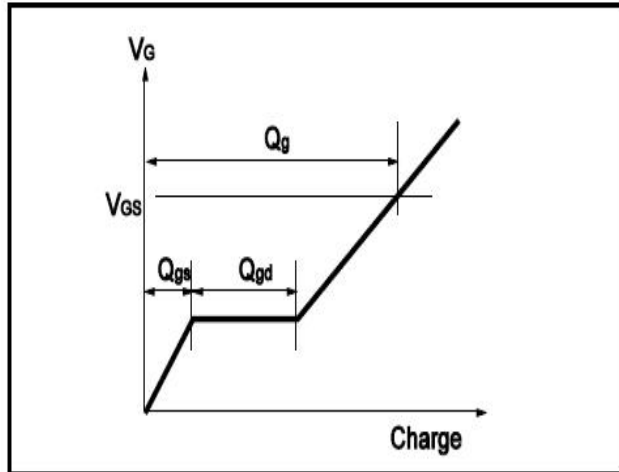


Fig.9 Switching Time Measurement Circuit

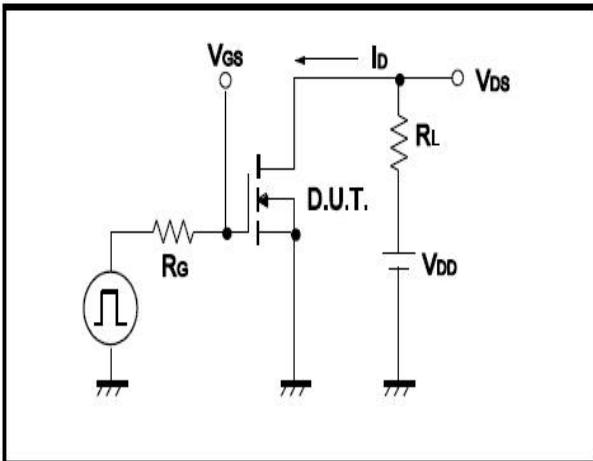


Fig.10 Gate Charge Waveform

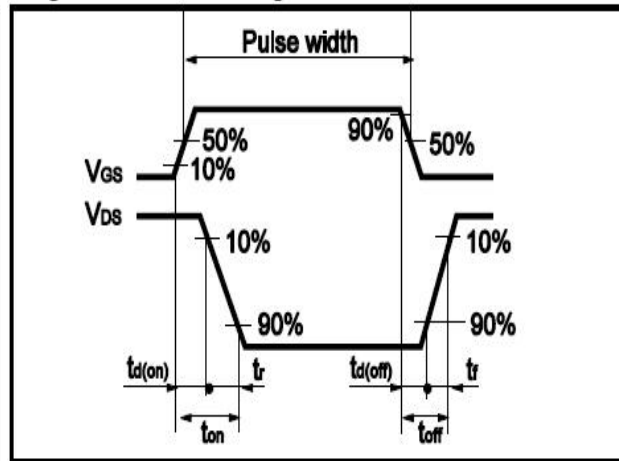


Fig.11 Avalanche Measurement Circuit

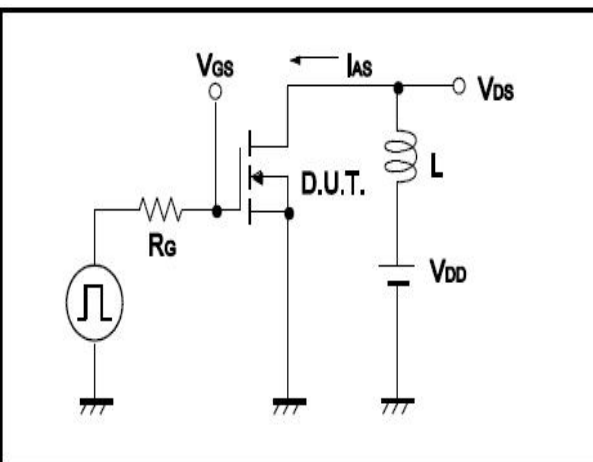
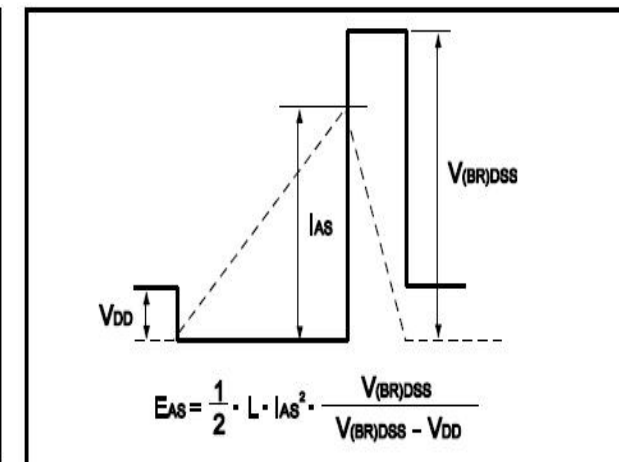
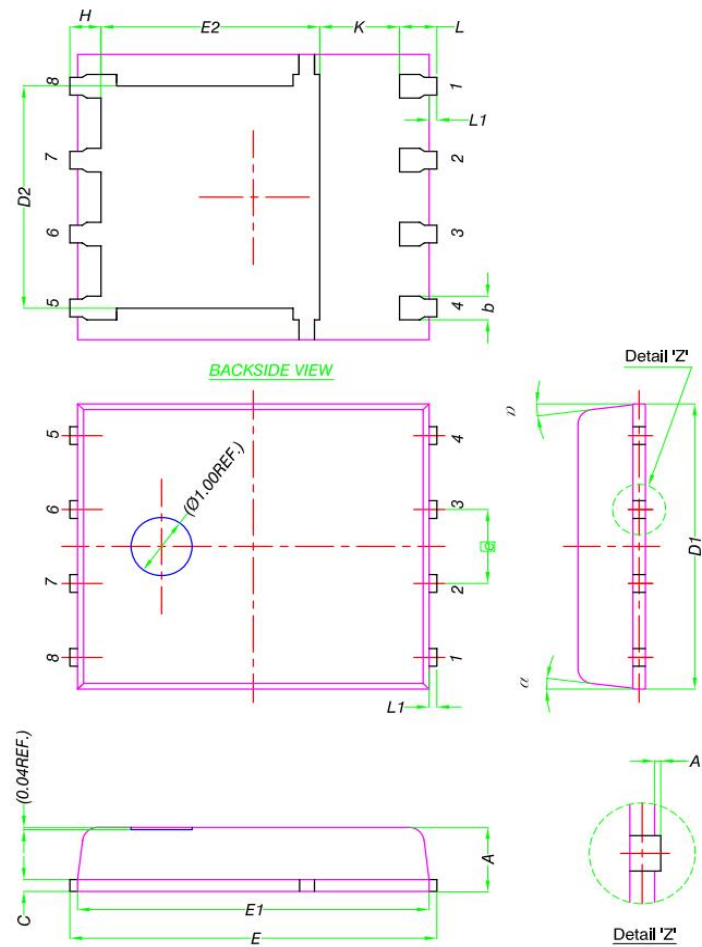


Fig.12 Avalanche Waveform



**•Dimensions (DFN5×6)**

Unit: mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°